

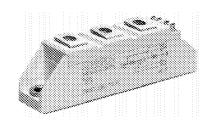


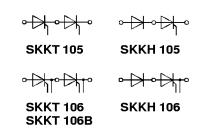
$V_{RSM}$	$V_{RRM}$	(dv/	I <sub>TRMS</sub> (maximum value for continuous operation)				
	$V_{DRM}$	dt) <sub>cr</sub>	180 A				
			$I_{TAV}$ (sin. 180; $T_{case} = 80  ^{\circ}$ C)				
V	V	V/μs	115 A				
500	400	500	-	_	SKKH 105/04 D	-	
700	600	500	SKKT 105/06 D	SKKT 106/06 D	_	SKKH 106/06 D	
900	800	500	SKKT 105/08 D	SKKT 106/08 D <sup>1)</sup>	SKKH 105/08 D	SKKH 106/08 D	
1300	1200	1000	SKKT 105/12 E	SKKT 106/12 E <sup>1)</sup>	SKKH 105/12 E	SKKH 106/12 E	
1500	1400	1000	SKKT 105/14 E	SKKT 106/14 E <sup>1)</sup>	SKKH 105/14 E	SKKH 106/14 E	
1700	1600	1000	SKKT 105/16 E	SKKT 106/16 E <sup>1)</sup>	SKKH 105/16 E	SKKH 106/16 E	
1900	1800	1000	SKKT 105/18 E	SKKT 106/18 E <sup>1)</sup>	SKKH 105/18 E	SKKH 106/18 E	

1900   180	0   1000   SKKT 105/18 E   SKKT 106/18	E''  SKKH 105/18 E   SKKH 1	106/18 E
Symbol	Conditions	SKKT 105 SKKH 105 SKKT 106B SKKH 106	Units
I <sub>TAV</sub>	sin. 180; T <sub>case</sub> = 85 °C	106	Α
I <sub>D</sub>	B2/B6   T <sub>amb</sub> = 35 °C; P 3/180 F	145 / 180	A
_	P 16/200 F	190 / 260	A
I <sub>RMS</sub>	W1/W3   T <sub>amb</sub> = 35 °C; P 3/180 F	200 / 3 x 140	A
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	2 250	Α
	T <sub>vi</sub> = 130 °C; 10 ms	1 900	A
i <sup>2</sup> t	T <sub>vi</sub> = 25 °C; 8,3 10 ms	25 000	A <sup>2</sup> s
	T <sub>vj</sub> = 130 °C; 8,3 10 ms	18 000	A <sup>2</sup> s
t <sub>gd</sub>	T <sub>vi</sub> = 25 °C; I <sub>G</sub> = 1 A		
•	$di_G/dt = 1 A/\mu s$	1	μs
$t_{gr}$	$V_D = 0.67 \cdot V_{DRM}$	2	μs
(di/dt) <sub>cr</sub>	T <sub>vj</sub> = 130 °C	150	A/μs
$t_q$	T <sub>vj</sub> = 130 °C	typ. 100	μs
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ./max.	150 / 250	mA
IL	$T_{vj} = 25  ^{\circ}\text{C}; R_G = 33  \Omega; \text{ typ./max.}$	300 / 600	mA
$V_T$	$T_{vj} = 25  ^{\circ}\text{C}; I_{T} = 300  \text{A}$	max. 1,65	V
$V_{T(TO)}$	T <sub>vj</sub> = 130 °C	0,9	V
$r_T$	T <sub>vj</sub> = 130 °C	2	mΩ
$I_{DD}$ ; $I_{RD}$	$T_{vj} = 130  ^{\circ}\text{C};  V_{RD} = V_{RRM}$		
	$V_{DD} = V_{DRM}$	max. 20	mA
$V_{GT}$	$T_{vj} = 25  ^{\circ}C; d.c.$	3	V
$I_{GT}$	$T_{vj} = 25  ^{\circ}\text{C}; \text{d.c.}$	150	mA
$V_{\sf GD}$	$T_{vj} = 130  ^{\circ}\text{C}; d.c.$	0,25	V
$I_{GD}$	T <sub>vj</sub> = 130 °C; d.c.	6	mA
$R_{thjc}$	cont.	0,28 / 0,14	°C/W
	sin. 180   per thyristor /	0,30 / 0,15	°C/W
_	rec. 120 per module	0,32 / 0,16	°C/W
R <sub>thch</sub>	,	0,2 / 0,1	°C/W
$T_{vj}$		- 40 + 130	°C
T <sub>stg</sub>		- 40 + 125	°C
$V_{isol}$	a. c. 50 Hz; r.m.s; 1 s/1 min	3600 / 3000	V~
M <sub>1</sub>	to heatsink } SI (US) units	5 (44 lb. in.) $\pm$ 15 % <sup>2)</sup>	Nm
$M_2$	to terminals J	3 (26 lb. in.) ± 15 % <sup>2)</sup>	Nm
а		5 9.81	l m/s <sup>2</sup>

SEMIPACK® 1 **Thyristor / Diode Modules** 

**SKKT 105 SKKH 105 SKKT 106 SKKH 106 SKKT 106B** 





## **Features**

- · Heat transfer through aluminium oxide ceramic isolated metal baseplate
- · Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

## **Typical Applications**

- DC motor control (e.g. for machine tools)
- · AC motor soft starters
- Temperature control (e.g. for ovens, chemical processes)
- · Professional light dimming (studios, theaters)

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5 9,81

95

SKKT 106B: A 48

A 46

A 47

SKKT 106:

SKKH 106:

Nm m/s<sup>2</sup>

g

SKKT 105: A 5

SKKH 105: A 6

а

w

Case

approx.

 $\rightarrow$  page B 1 – 95

<sup>1)</sup> Also available in SKKT 106 B configuration (case A 48)

<sup>&</sup>lt;sup>2)</sup> See the assembly instructions

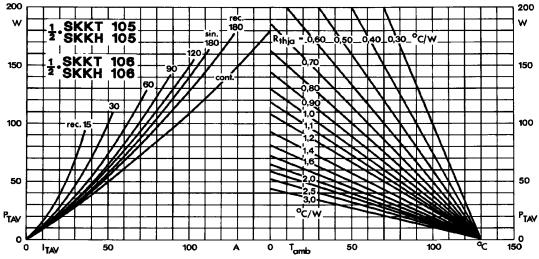


Fig. 1 Power dissipation per thyristor vs. on-state current and ambient temperature

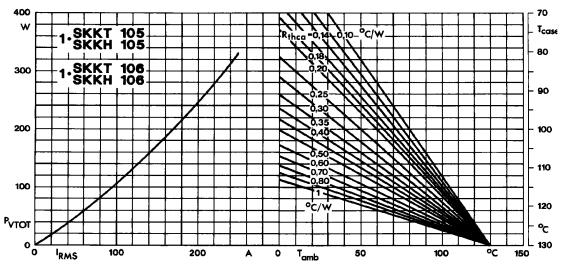


Fig. 2 Power dissipation per module vs. rms current and case temperature

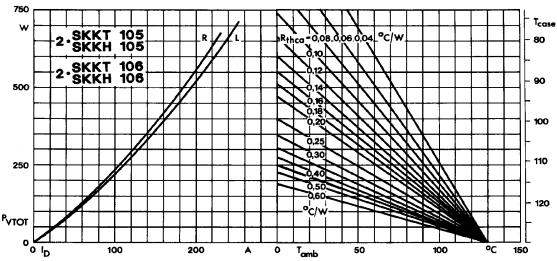


Fig. 3 Power dissipation of two modules vs. direct current and case temperature

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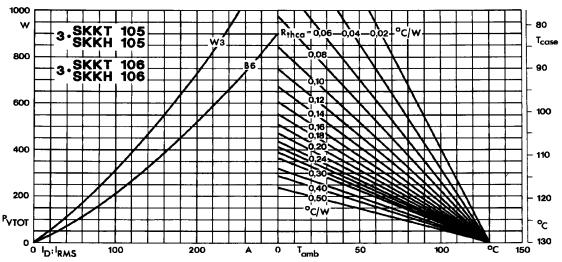


Fig. 4 Power dissipation of three modules vs. direct and rms current and case temperature

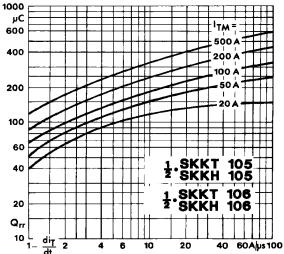


Fig. 5 Recovered charge vs. current decrease

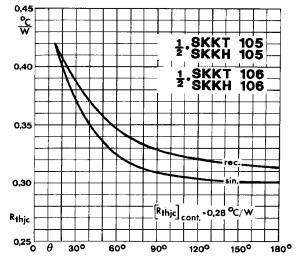


Fig. 7 Thermal resistance vs. conduction angle

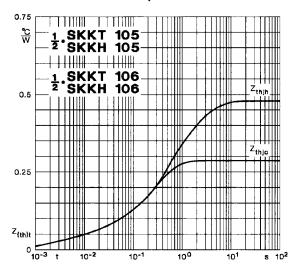


Fig. 6 Transient thermal impedance vs. time

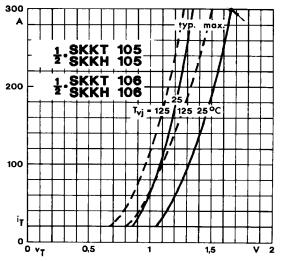


Fig. 8 On-state characteristics

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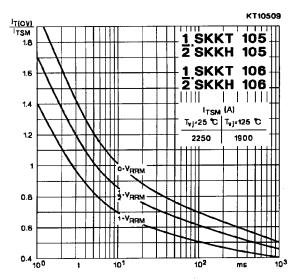


Fig. 9 Surge overload current vs. time

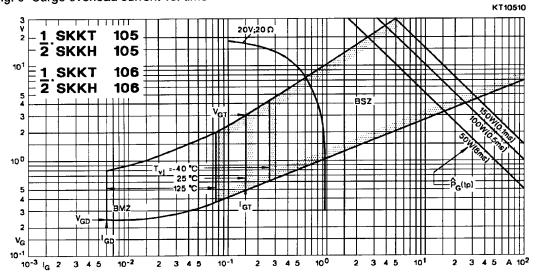


Fig. 10 Gate trigger characteristics

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